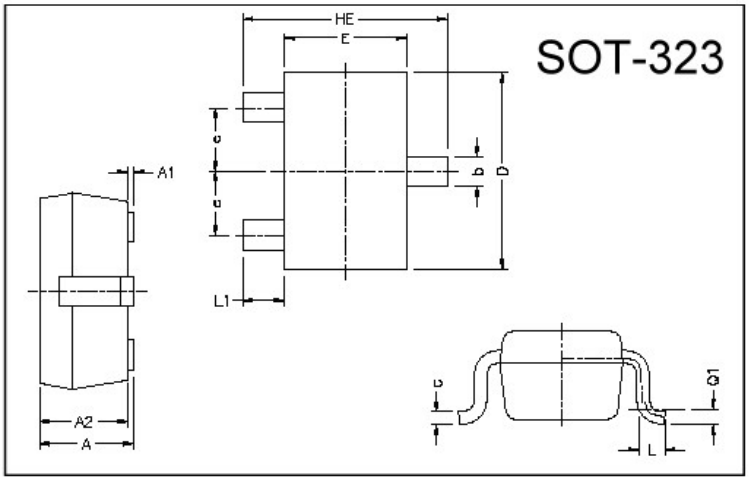
GS123

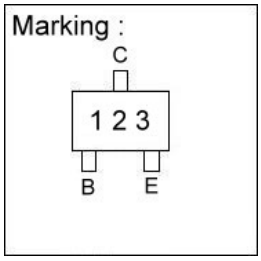
NPN EPITAXIAL TRANSISTOR

Description

The GS123 is designed for general purpose amplifier applications.

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.80	1.10	L1	0.42 REF.	
A1	0	0.10	L	0.15	0.35
A2	0.80	1.00	b	0.25	0.40
D	1.80	2.20	c	0.10	0.25
E	1.15	1.35	e	0.65 REF.	
HE	1.80	2.40	Q1	0.15 BSC.	

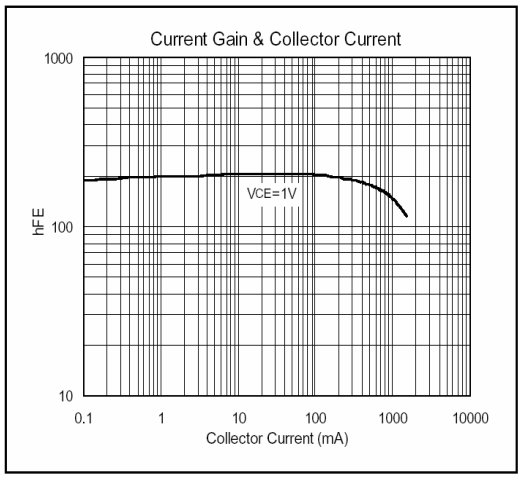
Absolute Maximum Ratings at Ta = 25℃

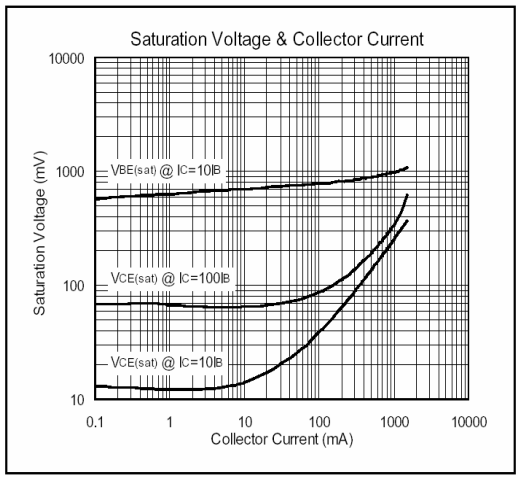
Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	℃
Storage Temperature	Tstg	-55 ~ +150	℃
Collector to Base Voltage	VCBO	25	V
Collector to Emitter Voltage	VCEO	20	V
Emitter to Base Voltage	VEBO	5	V
Collector Current	IC	700	mA
Total Power Dissipation	PD	225	mW

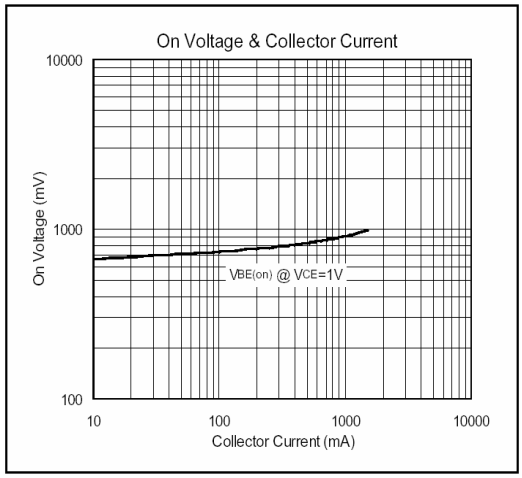
Characteristics at Ta = 25℃

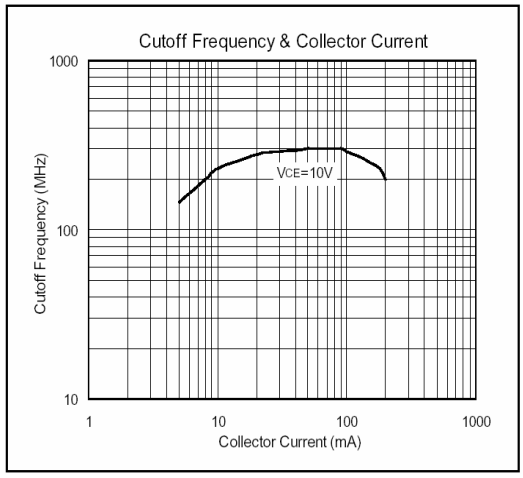
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	25	-	-	V	IC=10uA , IE=0
BVCEO	20	-	-	V	IC=1mA, IB=0
BVEBO	5	-	-	V	IE=10uA, IC=0
ICBO	-	-	1	uA	VCB=20V, IE=0
VCE(sat)	-	-	400	mV	IC=500mA, IB=50mA
VBE(on)	-	-	1	V	VCE=1V, IC=150mA
hFE	150	-	300		VCE=1V, IC=150mA
fT	150	-	-	MHz	VCE=10V, IC=20mA, f=100MHz
Cob	-	-	10	pF	VCB=10V, f=1MHz

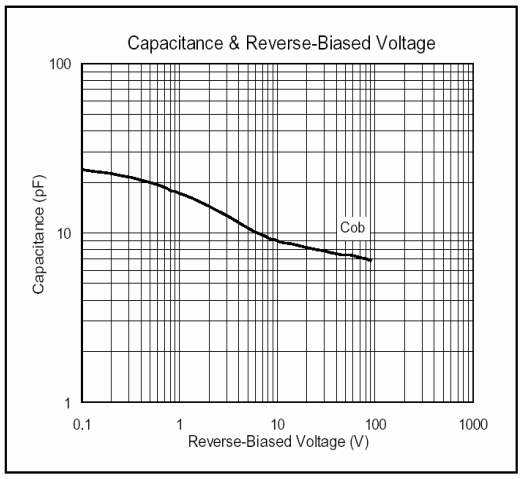
Characteristics Curve

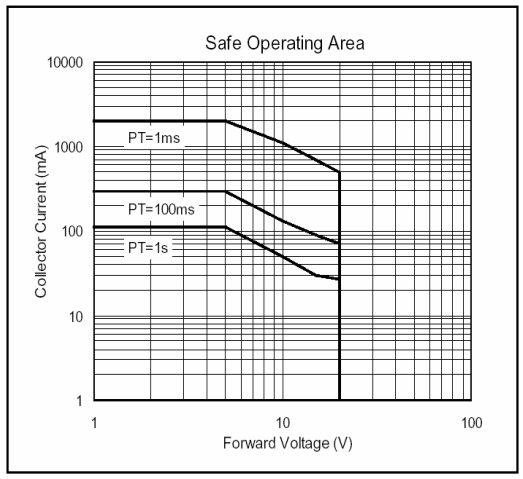












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